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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET

PDTA123E series PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Product data sheet Supersedes data of 2004 Apr 07 2004 Aug 02



PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

FEATURES

- Built-in bias resistors
- · Simplified circuit design
- Reduction of component count
- · Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- · Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	_	-50	V
Io	output current (DC)	_	-100	mA
R1	bias resistor	2.2	_	kΩ
R2	bias resistor	2.2	_	kΩ

DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACI	KAGE	MARKING CODE	NDN COMPLEMENT	
ITPE NUMBER	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT	
PDTA123EE	SOT416	SC-75	5C	PDTC123EE	
PDTA123EEF	SOT490	SC-89	6C	PDTC123EEF	
PDTA123EK	SOT346	SC-59	42	PDTC123EK	
PDTA123EM	SOT883	SC-101	F7	PDTC123EM	
PDTA123ES	SOT54 (TO-92)	SC-43	TA123E	PDTC123ES	
PDTA123ET	SOT23	_	*21 ⁽¹⁾	PDTC123ET	
PDTA123EU	SOT323	SC-70	*42 ⁽¹⁾	PDTC123EU	

Note

^{1. * =} p: Made in Hong Kong.

^{* =} t: Made in Malaysia.

^{* =} W: Made in China.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	CIMPLIFIED OUTLINE AND CVMPOL		PINNING
TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION
PDTA123ES	R1	1 2 3	base collector emitter
PDTA123EE PDTA123EEF PDTA123EK PDTA123ET PDTA123EU	Top view 1 R1 R2 R2 R2 R2 RDB271	1 2 3	base emitter collector
PDTA123EM	2 R1 R2 R2 RDB267	1 2 3	base emitter collector

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE								
ITPE NUMBER	NAME DESCRIPTION								
PDTA123EE	_	plastic surface mounted package; 3 leads	SOT416						
PDTA123EEF	_	plastic surface mounted package; 3 leads	SOT490						
PDTA123EK	_	plastic surface mounted package; 3 leads	SOT346						
PDTA123EM	_	leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm	SOT883						
PDTA123ES	_	plastic single-ended leaded (through hole) package; 3 leads	SOT54						
PDTA123ET	_	plastic surface mounted package; 3 leads	SOT23						
PDTA123EU	_	plastic surface mounted package; 3 leads	SOT323						

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-50	V
V _{CEO}	collector-emitter voltage	open base	_	-50	V
V _{EBO}	emitter-base voltage	open collector	_	-10	V
VI	input voltage				
	positive		_	+10	V
	negative		_	-12	V
Io	output current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	_	500	mW
	SOT23	note 1	_	250	mW
	SOT346	note 1	_	250	mW
	SOT323	note 1	_	200	mW
	SOT416	note 1	_	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	830	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	_	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	_	_	-1	μΑ
		$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	_	_	-2	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}$	30	_	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	_	-150	mV
$V_{i(off)}$	input-off voltage	$I_C = -1 \text{ mA}; V_{CE} = -5 \text{ V}$	_	-1.2	-0.5	V
$V_{i(on)}$	input-on voltage	$I_C = -20 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-2	-1.6	_	V
R1	input resistor		1.54	2.2	2.86	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$I_E = I_e = 0 \text{ A}; V_{CB} = -10 \text{ V};$ f = 1 MHz	_	_	3	pF

PNP resistor-equipped transistors; $R1 = 2.2 \text{ k}\Omega$, $R2 = 2.2 \text{ k}\Omega$

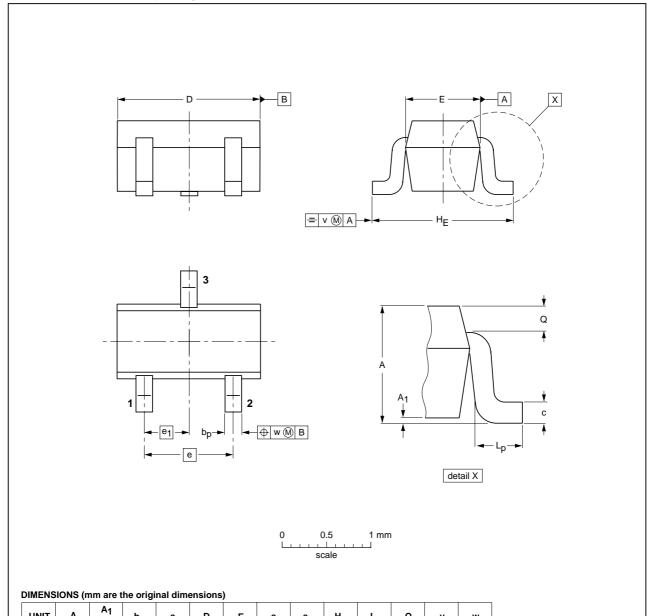
PDTA123E series

PACKAGE OUTLINES

UNIT

Plastic surface-mounted package; 3 leads

SOT416



								DEEEDE	NCES					
().6() (0.15 0.10 1.4 0.7 1.45 0.15 0.13		0.60		0.10	0.10	17	0.7			1.40	0.10	0.10		

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE		
SOT416			SC-75		-04-11-04 06-03-16		

 H_{E}

 $L_{\mathbf{p}}$

Q

2004 Aug 02 6

bp

1.8

max

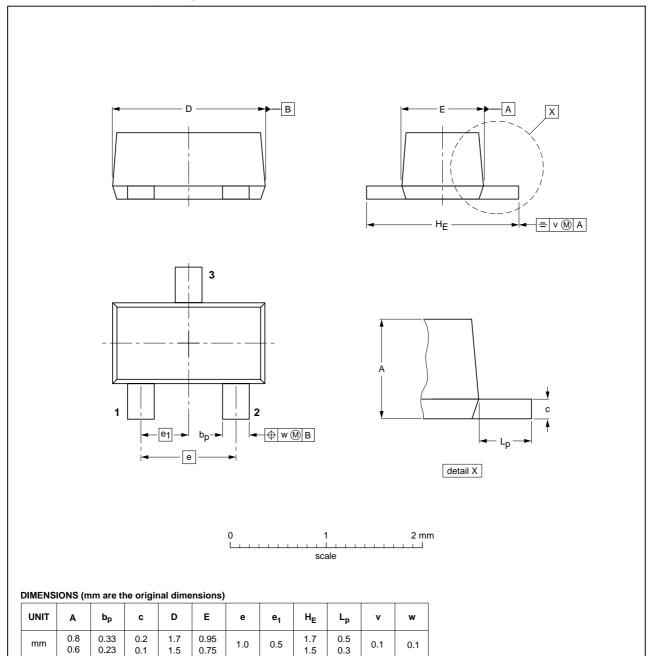
0.1

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT490



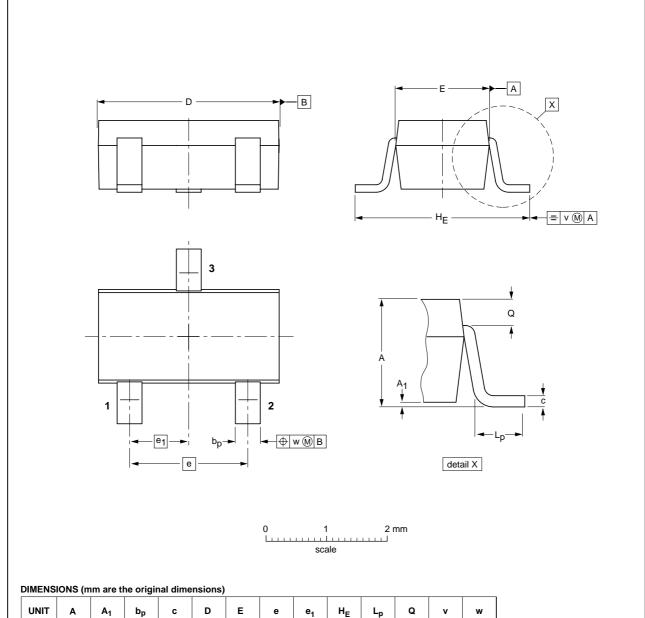
OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE		
SOT490			SC-89		05-07-28 06-03-16		

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT346



UNIT	Α	A ₁	bp	С	D	E	е	e ₁	HE	Lp	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

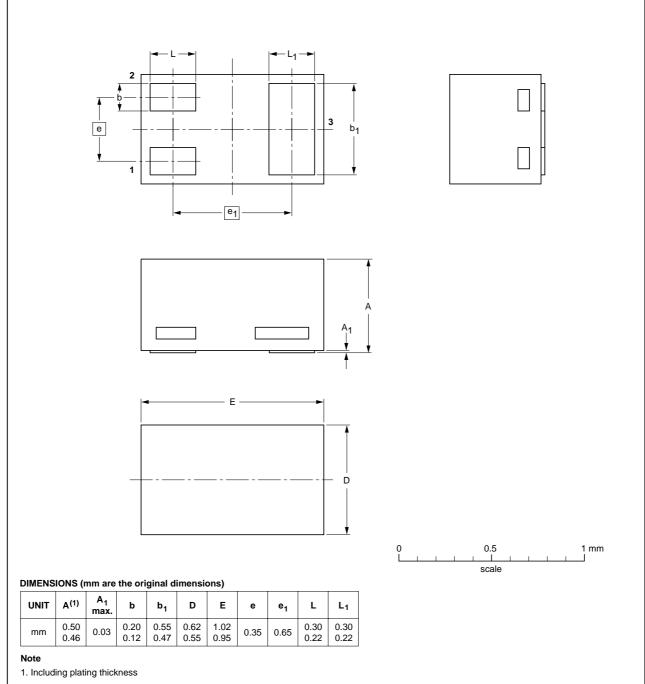
OUTLINE		REFER	EUROPEAN	ICCUIT DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT346		TO-236	SC-59A			-04-11-11 06-03-16	

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



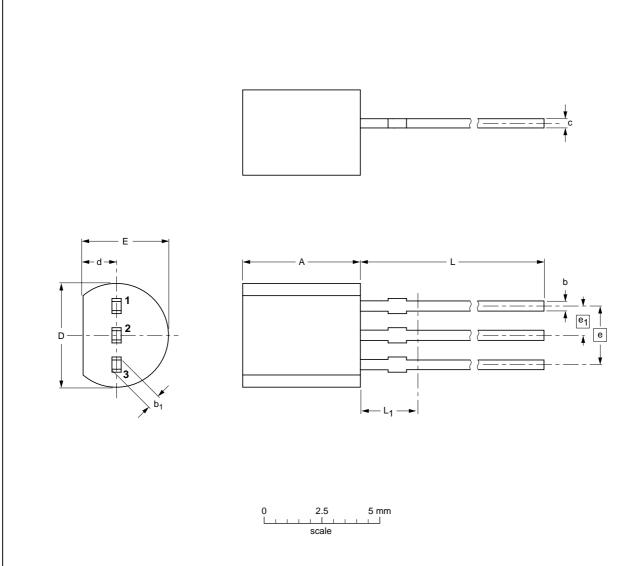
OUTLINE		EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			03-02-05 03-04-03

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	Α	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

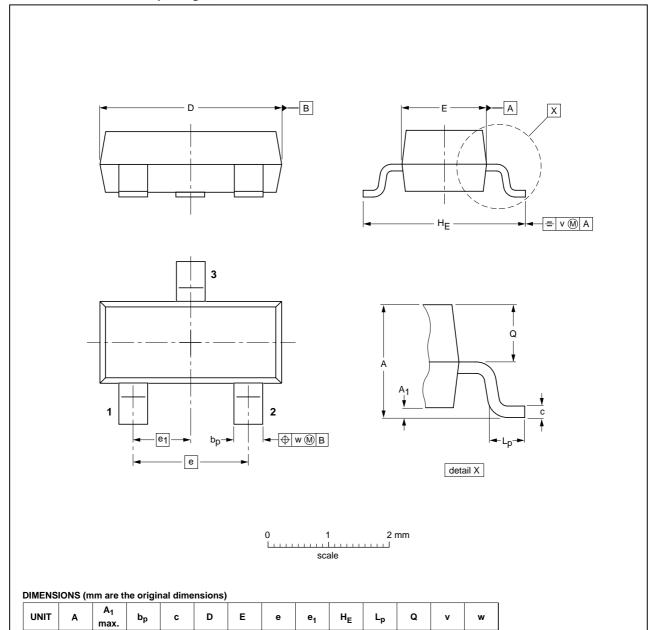
OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A			04-06-28 04-11-16

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE		REFER	EUROPEAN	ICCUE DATE			
VERSION	VERSION IEC		JEITA		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				-04-11-04 06-03-16	

1.9

0.45

0.55

0.2

0.1

2004 Aug 02 11

0.48

0.38

0.15

1.1

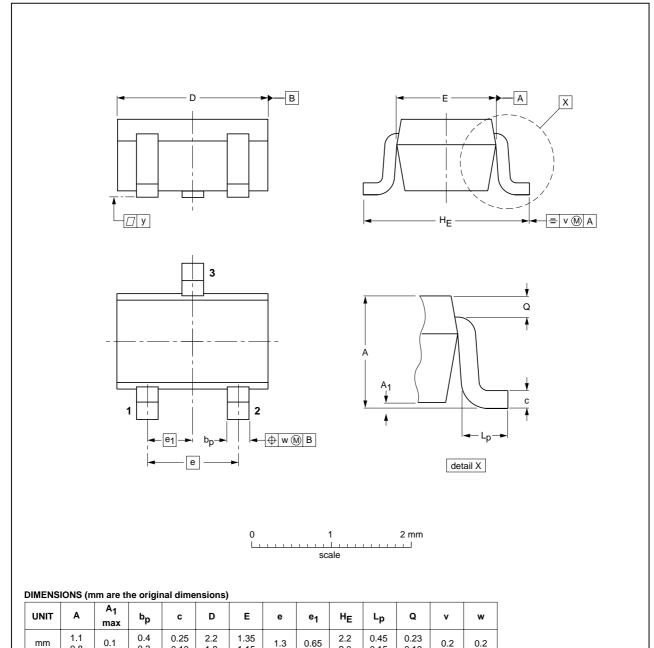
0.9

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

Plastic surface-mounted package; 3 leads

SOT323



OUTLINE	OUTLINE REFERENCES					ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT323			SC-70			-04-11-04 06-03-16	

2004 Aug 02 12

0.3

PNP resistor-equipped transistors; R1 = 2.2 k Ω , R2 = 2.2 k Ω

PDTA123E series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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